

L Number	Hits	Search Text	DB	Time stamp.
-	1	6277679.pn.	DERWENT	2002/11/26 17:57
-	17	((("6242758") or ("6268695") or ("5953708") or ("5990542") or ("6169293") or ("6239470") or ("5010027") or ("5439837") or ("5441905") or ("5602047") or ("5637519") or ("5684365") or ("5685364") or ("5702960") or ("5719078") or ("5952708") or ("6063653")).PN.	USPAT; US-PGPUB	2002/11/26 19:01
-	4006	polyethylene\$1terephthalate	USPAT; US-PGPUB	2002/11/26 19:01
-	120	polyethylene\$1terephthalate and ((display near device) thin\$film\$transistor tft)	USPAT; US-PGPUB	2002/11/26 19:15
-	23	polyethylene\$1terephthalate and (thin\$film\$transistor tft)	USPAT; US-PGPUB	2002/11/26 19:19
-	247	(thin\$film\$transistor tft) and (top\$1gate)	USPAT; US-PGPUB	2002/11/26 19:20
-	32	((thin\$film\$transistor tft) and (top\$1gate)) and ((gate near insulat\$5) with nitride with oxide)	USPAT; US-PGPUB	2002/11/26 19:44
-	32	((thin\$film\$transistor tft) and (top\$1gate)) and ((gate near insulat\$5) with nitride with oxide)	USPAT; US-PGPUB	2002/11/26 19:56
-	2102	(gate near insulat\$5) with nitride with oxide	USPAT; US-PGPUB	2002/11/26 19:56
-	795	((gate near insulat\$5) with nitride with oxide) and (thin\$1film\$1transistor tft)	USPAT; US-PGPUB	2002/11/26 20:03
-	436	((gate near insulat\$5) with nitride with oxide) and (thin\$1film\$1transistor tft)) and organic	USPAT; US-PGPUB	2002/11/26 19:58
-	104	((gate near insulat\$5) with nitride with oxide) and (thin\$1film\$1transistor tft)) and (oxy\$1nitride)	USPAT; US-PGPUB	2002/11/26 19:59
-	1	((gate near insulat\$5) with nitride with oxide) and (thin\$1film\$1transistor tft)) and (oxy\$1nitride)) and ((organic near substrate) (resin near substrate))	USPAT; US-PGPUB	2002/11/26 20:01
-	18	((gate near insulat\$5) with nitride with oxide) and (thin\$1film\$1transistor tft)) and ((organic near substrate) (resin near substrate))	USPAT; US-PGPUB	2002/11/26 20:01
-	178	(thin\$1film\$1transistor tft) and ((gate near insulat\$5) with oxy\$1nitride)	USPAT; US-PGPUB	2002/11/26 20:05
-	4	((thin\$1film\$1transistor tft) and ((gate near insulat\$5) with oxy\$1nitride)) and top\$1gate	USPAT; US-PGPUB	2002/11/26 20:04
-	496	(gate near insulat\$5) with oxy\$1nitride	USPAT; US-PGPUB	2002/11/26 20:06
-	76	((gate near insulat\$5) with oxy\$1nitride) with (silicon adj oxide) with (silicon adj nitride)	USPAT; US-PGPUB	2002/11/26 20:06
-	31	((gate near insulat\$5) with oxy\$1nitride) with (silicon adj oxide) with (silicon adj nitride)) and (thin\$1film\$1transistor tft)	USPAT; US-PGPUB	2002/11/26 20:07
-	35	reverse\$2staggered reverse\$2gate	USPAT; US-PGPUB	2002/11/26 21:18
-	26	(reverse\$2staggered reverse\$2gate) and channel	USPAT; US-PGPUB	2002/11/26 21:19
-	21	((reverse\$2staggered reverse\$2gate) and channel) and (thin\$1film\$1transistor tft)	USPAT; US-PGPUB	2002/11/26 21:19
-	24840	acrylic adj resin	USPAT; US-PGPUB	2002/11/27 13:28
-	369	(acrylic adj resin) with nitride	USPAT; US-PGPUB	2002/11/27 13:28
-	253	((acrylic adj resin) with nitride) with oxide	USPAT; US-PGPUB	2002/11/27 13:29
-	61	((acrylic adj resin) with nitride) with oxide) and (thin\$1film\$1transistor tft)	USPAT; US-PGPUB	2002/11/27 13:29